

# **NCE N-Channel Super Trench II Power MOSFET**

### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **Application**

- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

#### **General Features**

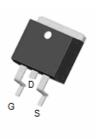
- $V_{DS}$  =120V, $I_D$  =190A  $R_{DS(ON)}$ =3.0m $\Omega$  , typical (TO-220)@  $V_{GS}$ =10V  $R_{DS(ON)}$ =2.8m $\Omega$  , typical (TO-263)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

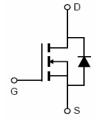
100% UIS TESTED! 100% ΔVds TESTED!

**TO-220** 



**TO-263** 





**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP035N12	NCEP035N12	TO-220	-	-	-
NCEP035N12D	NCEP035N12D	TO-263-2L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	120	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	190	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	135	А
Pulsed Drain Current	I <sub>DM</sub>	760	А
Maximum Power Dissipation	P <sub>D</sub>	300	W
Derating factor		2	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	2300	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance.Junction-to-Case <sup>(Note 2)</sup>	D	0.5	°C/W
Thermal Resistance, Junction-to-Case	<b>K</b> θJC	0.5	CIVV



Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

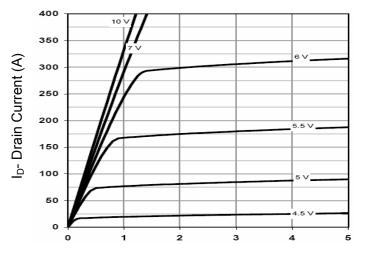
Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics				•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA		120		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =120V,V <sub>GS</sub> =0V		-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V		-	-	±100	nA
On Characteristics (Note 3)				•	•		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	50μΑ	2.0	3.0	4.0	V
Danie Course On Otata Basistana	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =95A	TO-220	-	3.0	3.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		TO-263		2.8	3.5	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =95A			90	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V, F=1.0MHz		-	12700	-	PF
Output Capacitance	Coss			-	870	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	48	-	PF
Switching Characteristics (Note 4)				•	•		
Turn-on Delay Time	t <sub>d(on)</sub>			-	34	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =60V, $I_{D}$ =95A		-	27	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$		-	78	-	nS
Turn-Off Fall Time	t <sub>f</sub>			-	30	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =50V,I <sub>D</sub> =95A, V <sub>GS</sub> =10V		-	213	-	nC
Gate-Source Charge	Q <sub>gs</sub>			-	58		nC
Gate-Drain Charge	$Q_{gd}$			-	58		nC
Drain-Source Diode Characteristics				•	•	<u> </u>	
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =95A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	190	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =	: 100A	-	101	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs <sup>(Note3)</sup>		-	280	-	nC

#### Notes:

- ${\bf 1.}\ {\bf Repetitive}\ {\bf Rating:}\ {\bf Pulse}\ {\bf width}\ {\bf limited}\ {\bf by}\ {\bf maximum}\ {\bf junction}\ {\bf temperature}.$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=60V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

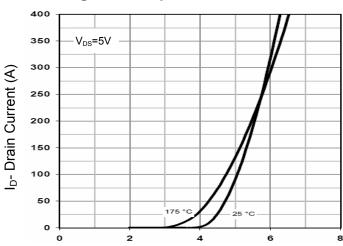


## **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)

**Figure 1 Output Characteristics** 



Vgs Gate-Source Voltage (V)

**Figure 2 Transfer Characteristics** 

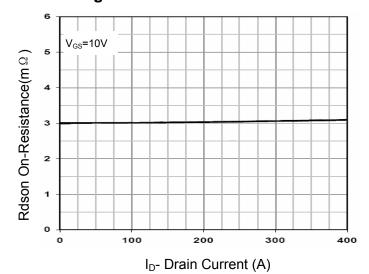
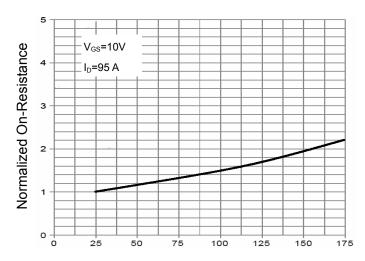
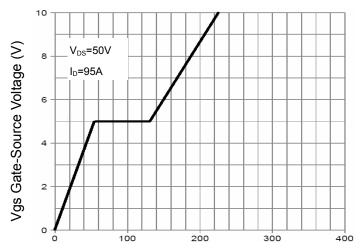


Figure 3 Rdson- Drain Current

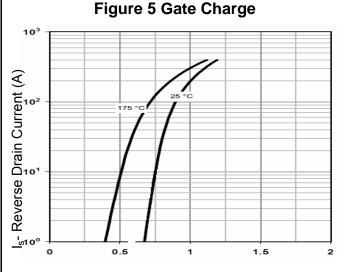


T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



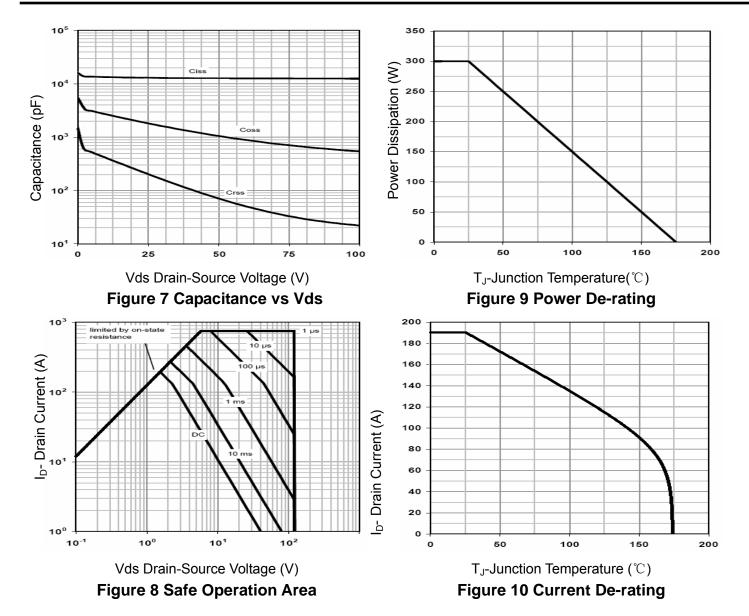
Qg Gate Charge (nC)

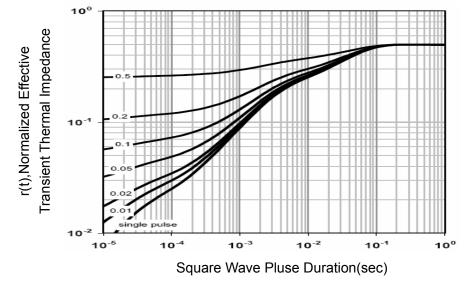


Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



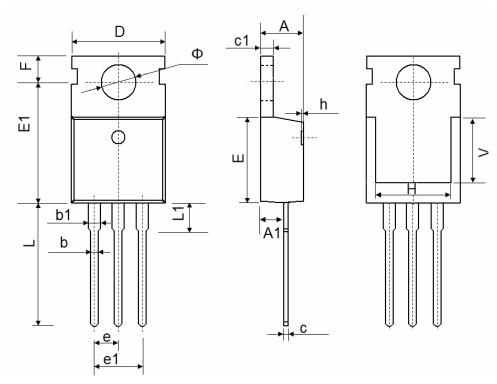




**Figure 11 Normalized Maximum Transient Thermal Impedance** 



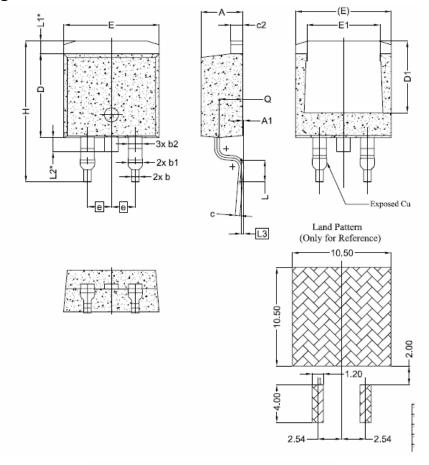
# **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Ф	3.400	3.800	0.134	0.150	



# **TO-263-2L Package Information**



SYMBOL	DIMENSIONS				
STIMBOL	MIN.	NOM.	MAX.		
А	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1,20	1,45	1,70		
С	0.40	0.40 0.50			
c2	1,15	1,27	1,40		
D	8.82	8.82 8.92			
D1	6.86 7.65		_		
E	9.96 10.16		10.36		
E1	6.89 7.77		7.89		
е	2.54 BSC				
Н	14,61	14,61 15,00			
L	1.78 2.32		2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.70			

# 新加車 CEPOWER

# NCEP035N12,NCEP035N12D

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